

# RS1001FL~RS1008FL

**GM** GarboMicro  
Semiconductor

## SMALL SURFACE MOUNT FAST DIODES

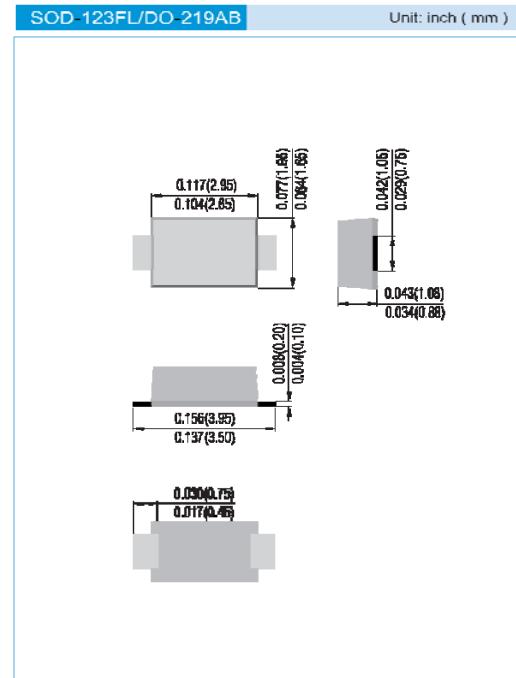
VOLTAGE 100 to 800 Volts CURRENT 1.0 Amperes

### FEATURES

- For surface mounted applications
- Low profile package
- Ideal for automated placement
- Glass Passivated Chip Junction
- High temperature soldering : 260°C / 10 seconds at terminals
- Pb free product : 99% Sn above can meet RoHS environment substance directive request

### MECHANICAL DATA

- Case: JEDEC DO-219AB,Molded plastic over passivated junction
- Terminals: Solderable per MIL-STD-750, Method 2026
- Standard Packaging : 8mm tape (EIA-481)
- Approx. Weight: 0.0168 gram



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%

Rating	Test condition	Symbol	RS1001FL	RS1002FL	RS1004FL	RS1006FL	RS1008FL	Units
Maximum repetitive peak reverse voltage		$V_{RRM}$	100	200	400	600	800	V
Maximum RMS voltage		$V_{RMS}$	70	140	280	420	560	V
Maximum DC blocking voltage		$V_{DC}$	100	200	400	600	800	V
Maximum average forward rectified current	$T_A=65^\circ C$ $T_A=45^\circ C$	$I_{F(AV)}$			1.4 0.5			A
Maximum instantaneous forward voltage	0.7A	$V_F$			1.15			V
Maximum DC reverse current at rated DC blocking voltage	$T_A=25^\circ C$ $T_A=125^\circ C$	$I_R$			10 50			$\mu A$
Thermal resistance junction to ambient air		$R_{\text{SJA}}$			180			K/W
Operating junction and storage temperature range		$T_J, T_{STG}$			-50 TO +150			$^\circ C$
Reverse recovery time	$I_F=0.5A$ $I_F=1A$ $t_{rr}=0.25A$	$t_{rr}$		150		250	500	nS
Typical capacitance	4V,1MHz	$C_J$		9				pF

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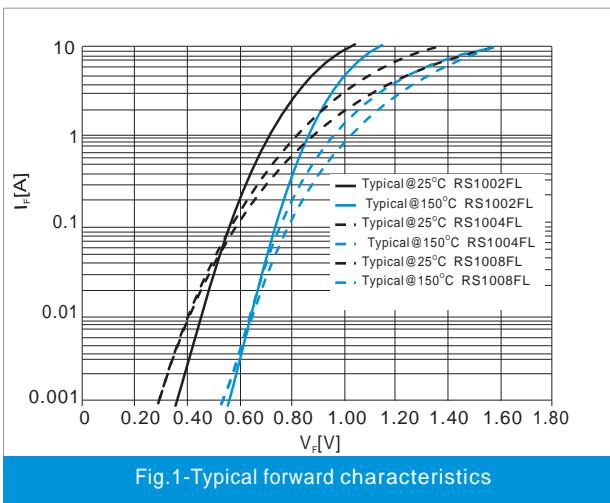


Fig.1-Typical forward characteristics

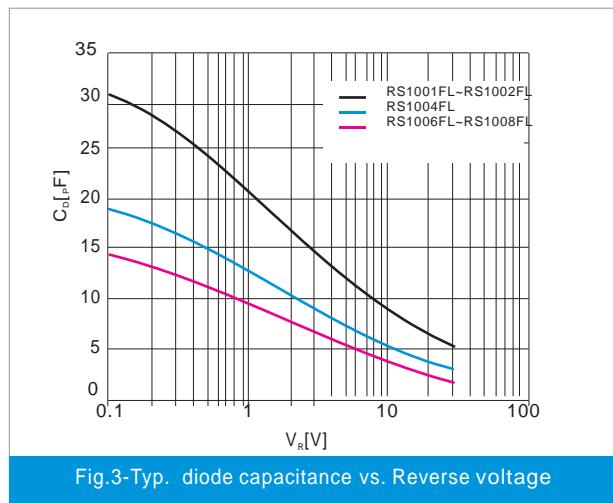


Fig.3-Typ. diode capacitance vs. Reverse voltage

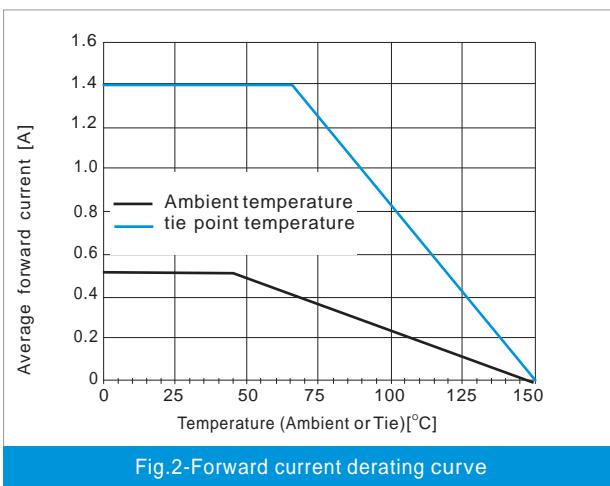


Fig.2-Forward current derating curve